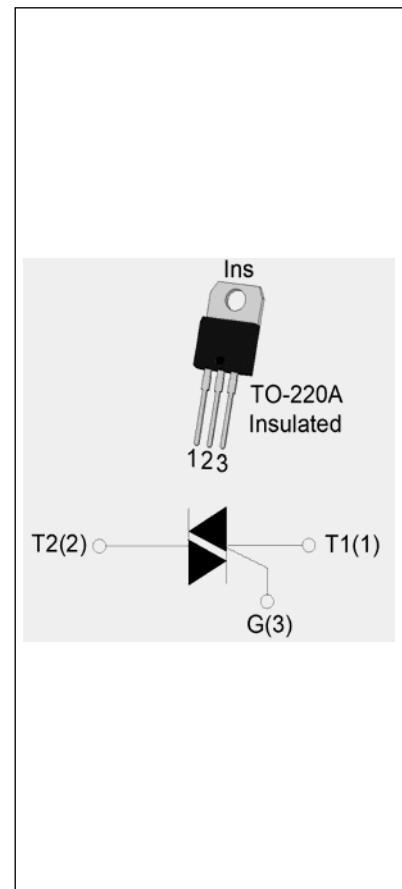




The T0810H-8A triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T0810H-8A provides a very high switching capability up to junction temperatures of 150°C. It can be driven directly through the MCU I/O port. By using an internal ceramic pad, T0810H-8A provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	800	V
$I_{GT} / /$	10/10/10	mA

Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-150	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c = 118^\circ\text{C}$)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	80	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		88	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	32	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100\text{Hz}$, $T_j=150^\circ\text{C}$)	di/dt	50	$A/\mu s$



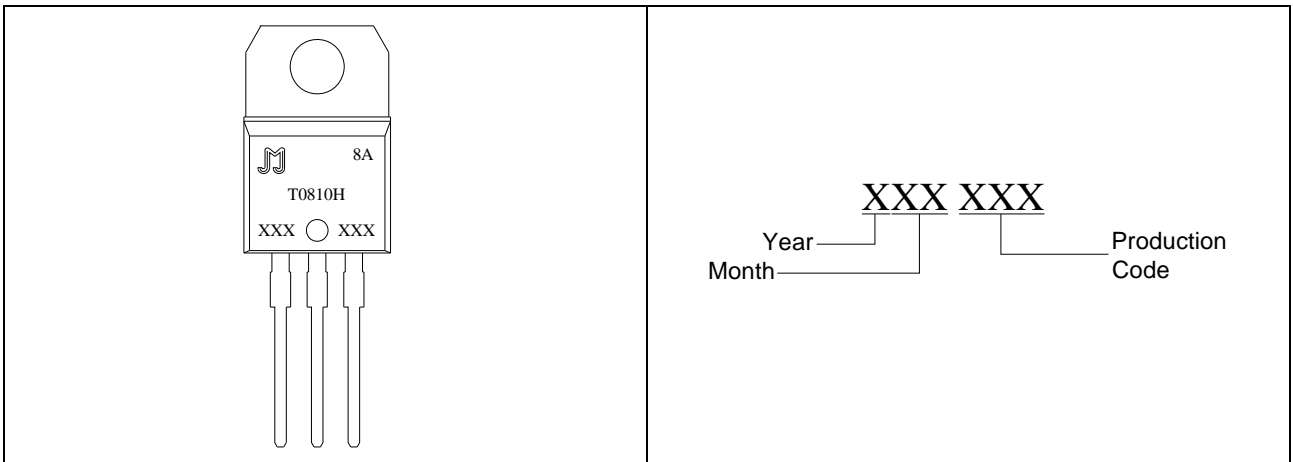
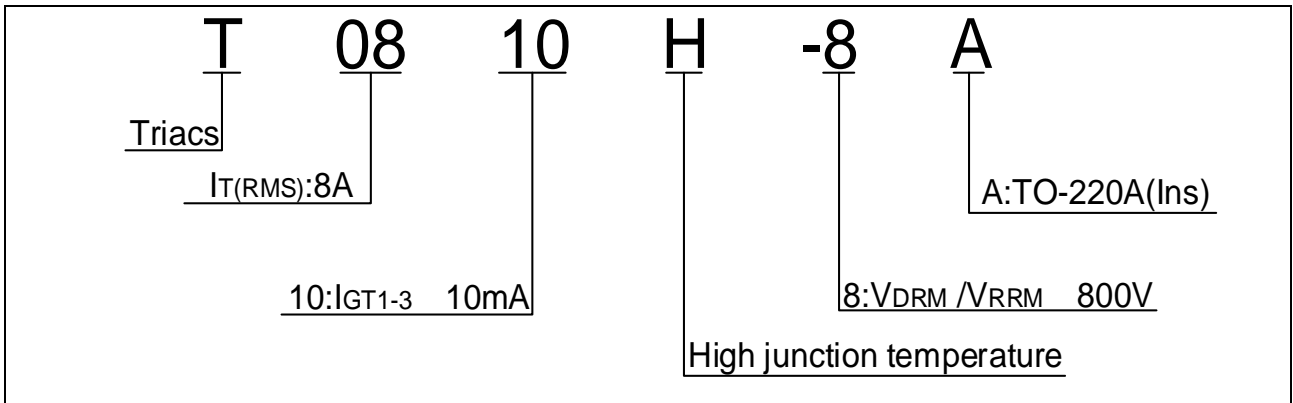
Peak gate current ($t_p=20\mu s$, $T_j=150$)	I_{GM}	4	A
Average gate power dissipation ($T_j=150$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	2.5	kV

($T_j=25$ unless otherwise specified)

I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3K$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	25	mA
				40	
I_H	$I_T=100mA$		MAX.	25	mA
dV/dt	$V_D=540V$ Gate Open $T_j=150$		MIN.	150	$V/\mu s$
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s$, $T_j=150$		MIN.	1.8	A/ms
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	2.5	μs
t_{off}				25	

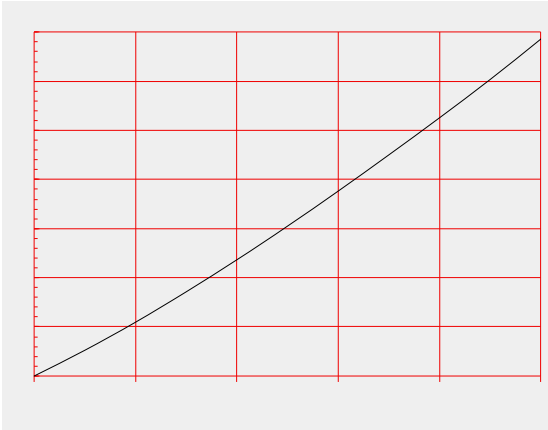
V_{TM}	$I_{TM}=11A$ $t_p=380\mu s$	$T_j=25$	1.4	V
V_{TO}	Threshold voltage	$T_j=150$	0.79	V
R_D	Dynamic resistance	$T_j=150$	51	m
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=150$	1.5	mA

$R_{th(j-c)}$	junction to case (AC)	3	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W -

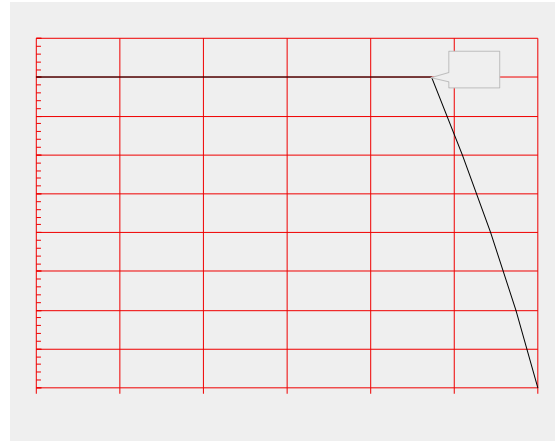




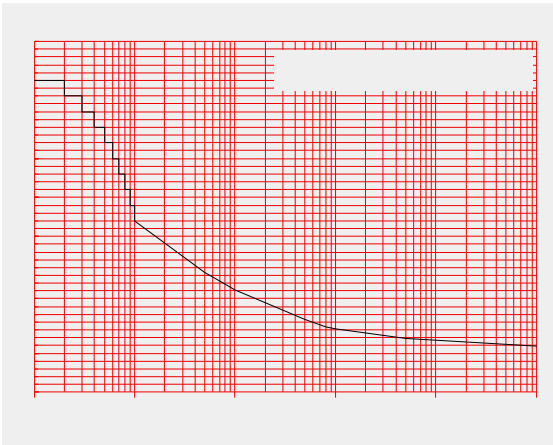
Maximum power dissipation versus RMS on-state current



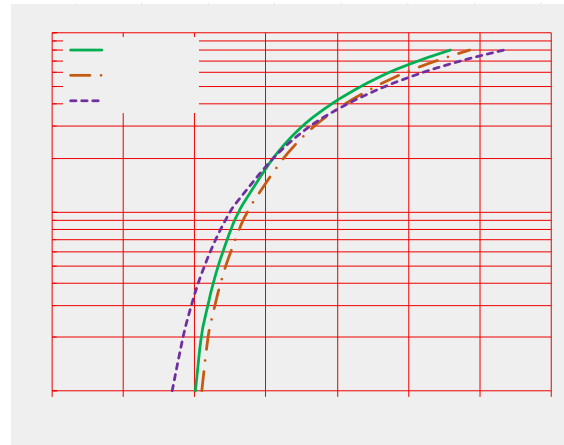
RMS on-state current versus case temperature



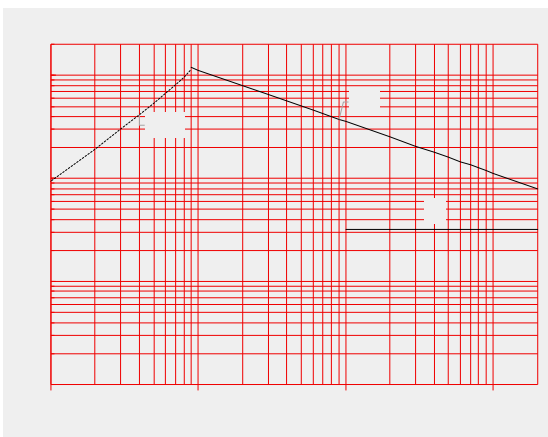
Surge peak on-state current versus number of cycles



On-state characteristics



Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($dI/dt < 50\text{A}/\mu\text{s}$)



Relative variations of gate trigger current, holding current and latching current versus junction temperature

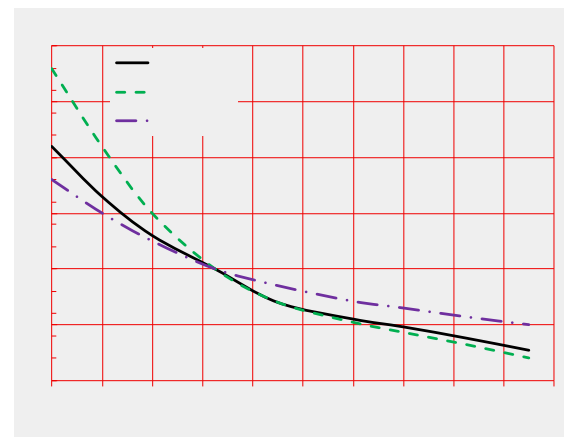
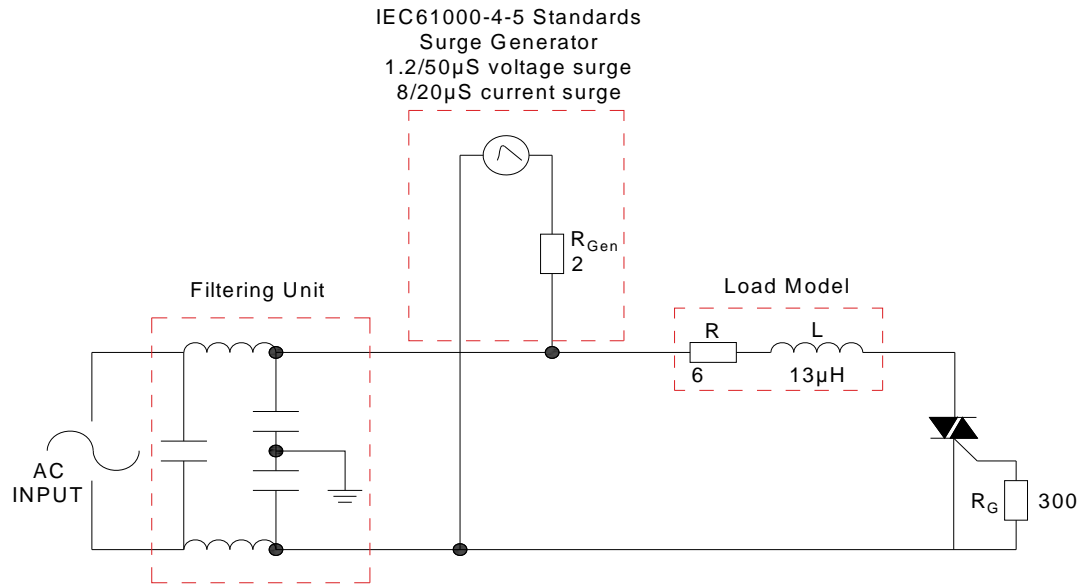




FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards





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Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated



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